Vishay Semiconductors

COMPLIANT

HALOGEN

Thyristor High Voltage, Surface Mount Phase Control SCR, 16 A



PRIMARY CHARACTERISTICS							
I _{T(AV)}	10 A						
V _{DRM} /V _{RRM}	800 V, 1200 V						
V_{TM}	1.4 V						
I _{GT}	60 mA						
T _J	-40 °C to 125 °C						
Package	D ² PAK (TO-263AB)						
Circuit configuration	Single SCR						

FEATURES

 Meets MSL level 1, per J-STD-020, LF maximum peak of 245 °C

 Designed and qualified according JEDEC®-JESD 47

 Material categorization: for definitions of compliance please see www.vishay.com/doc?99912

APPLICATIONS

- Input rectification (soft start)
- Vishay input diodes, switches and output rectifiers which are available in identical package outlines

DESCRIPTION

The VS-16TTS..S-M3 high voltage series of silicon controlled rectifiers are specifically designed for medium power switching and phase control applications. The glass passivation technology used has reliable operation up to 125 °C junction temperature.

OUTPUT CURRENT IN TYPICAL APPLICATIONS									
APPLICATIONS SINGLE-PHASE BRIDGE THREE-PHASE BRIDGE UNITS									
NEMA FR-4 or G-10 glass fabric-based epoxy with 4 oz. (140 µm) copper	2.5	3.5							
Aluminum IMS, R _{thCA} = 15 °C/W	6.3	9.5	A						
Aluminum IMS with heatsink, R _{thCA} = 5 °C/W	14.0	18.5							

Note

• T_A = 55 °C, T_J = 125 °C, footprint 300 mm²

MAJOR RATINGS AND CHARACTERISTICS								
PARAMETER	TEST CONDITIONS	VALUES	UNITS					
I _{T(AV)}	Sinusoidal waveform	10	A					
I _{RMS}		16	^					
V _{RRM} /V _{DRM}		800 to 1200	V					
I _{TSM}		200	Α					
V_{T}	10 A, T _J = 25 °C	1.4	V					
dV/dt		500	V/µs					
dI/dt		150	A/μs					
T _J		-40 to +125	°C					

VOLTAGE RATINGS									
PART NUMBER	V _{RRM} , MAXIMUM PEAK REVERSE VOLTAGE V	V _{DRM} , MAXIMUM PEAK DIRECT VOLTAGE V	I _{RRM} /I _{DRM} AT 125 °C mA						
VS-16TTS08S-M3	800	800	10						
VS-16TTS12S-M3	1200	1200	10						



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ABSOLUTE MAXIMUM RATINGS		T.		1		1	
PARAMETER	SYMBOL		TEST CONDITIONS	VAL	UNITS		
ADAMETER	OTMEGE		.ES. SCADITIONS			0.11.10	
Maximum average on-state current	I _{T(AV)}	$T_{\rm C} = 98 {}^{\circ}{\rm C}, {}^{2}$	80° conduction, half sine wave	1			
Maximum RMS on-state current	I _{RMS}			1	6	Α	
Maximum peak, one-cycle,		10 ms sine p	ulse, rated V _{RRM} applied	1	70	_ ^	
non-repetitive surge current	I _{TSM}	10 ms sine p	ulse, no voltage reapplied	20	00	1	
Maximum 12t for fusing	I ² t	10 ms sine p	ulse, rated V _{RRM} applied	144		A2-	
Maximum I ² t for fusing	1-1	10 ms sine p	200		- A ² s		
Maximum I ² √t for fusing	I²√t	t = 0.1 ms to	10 ms, no voltage reapplied	2000		A²√s	
Maximum on-state voltage drop	V_{TM}	10 A, T _J = 25	5 °C	1.4		V	
On-state slope resistance	r _t	T 105 %		24.0		mΩ	
Threshold voltage	V _{T(TO)}	IJ = 125 °C	T _J = 125 °C		.1	V	
Maximum various and direct lockers current	1 /1	T _J = 25 °C	$V_R = \text{rated } V_{RRM} / V_{DRM}$	0.5			
Maximum reverse and direct leakage current	I_{RM}/I_{DM}	T _J = 125 °C		1	0		
Holding current	I _H	Anode supply = 6 V, resistive load, initial I_T = 1 A, T_J = 25 °C		-	150	mA	
Maximum latching current	ΙL	Anode suppl	200		1		
Maximum rate of rise of off-state voltage	dV/dt	$T_J = T_J$ max. linear to 80 % $V_{DRM} = R_g - k = open$			500		
Maximum rate of rise of turned-on current	dl/dt				150		

TRIGGERING								
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS				
Maximum peak gate power	P _{GM}		8.0	W				
Maximum average gate power	P _{G(AV)}		2.0	VV				
Maximum peak positive gate current	+ I _{GM}		1.5	Α				
Maximum peak negative gate voltage	- V _{GM}		10	V				
		Anode supply = 6 V, resistive load, T _J = - 10 °C	90	mA				
Maximum required DC gate current to trigger	I _{GT}	Anode supply = 6 V, resistive load, T _J = 25 °C	60					
		Anode supply = 6 V, resistive load, T _J = 125 °C	35					
		Anode supply = 6 V, resistive load, T _J = - 10 °C	3.0					
Maximum required DC gate voltage to trigger	V_{GT}	Anode supply = 6 V, resistive load, T _J = 25 °C	2.0	V				
		Anode supply = 6 V, resistive load, T _J = 125 °C	1.0	V				
Maximum DC gate voltage not to trigger	V_{GD}	T = 105 °C V = Poted value	0.25					
Maximum DC gate current not to trigger	I _{GD}	T _J = 125 °C, V _{DRM} = Rated value	2.0	mA				

SWITCHING								
PARAMETER SYMBOL TEST CONDITIONS VALUES UN								
Typical turn-on time	t _{gt}	T _J = 25 °C	0.9					
Typical reverse recovery time	t _{rr}	T _{.I} = 125 °C	4	μs				
Typical turn-off time	t _q	1j = 125	110					

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THERMAL - MECHANICAL SPECIFICATIONS									
PARAMETER	METER SYMBOL TEST CONDITIONS								
Maximum junction and storage temperature range	T _J , T _{Stg}		-40 to +125	°C					
Maximum thermal resistance, junction to case	R _{thJC}	DC operation	1.3	°C/W					
Typical thermal resistance, junction to ambient	R _{thJA}	PCB mount (1)	40	C/VV					
Approximate weight			2	g					
Approximate weight			0.07	oz.					
Marking device		Case style D ² PAK (TO-263AB)	16TTS08S						
ividi kilig device		Case style D-FAR (10-203AB)	16TTS12S						

Note

⁽¹⁾ When mounted on 1" square (650 mm²) PCB of FR-4 or G-10 material 4 oz. (140 µm) copper 40 °C/W. For recommended footprint and soldering techniques refer to application note #AN-994

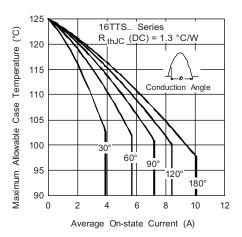


Fig. 1 - Current Rating Characteristics

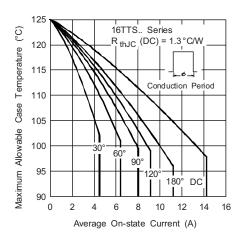


Fig. 2 - Current Rating Characteristics

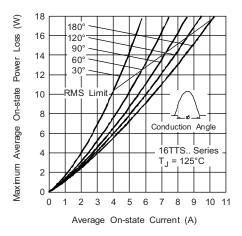


Fig. 3 - On-State Power Loss Characteristics

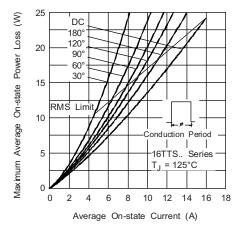


Fig. 4 - On-State Power Loss Characteristics

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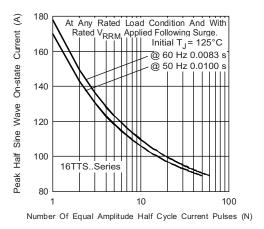


Fig. 5 - Maximum Non-Repetitive Surge Current

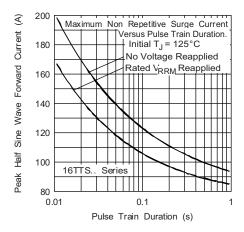


Fig. 6 - Maximum Non-Repetitive Surge Current

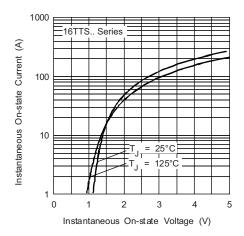


Fig. 7 - On-State Voltage Drop Characteristics

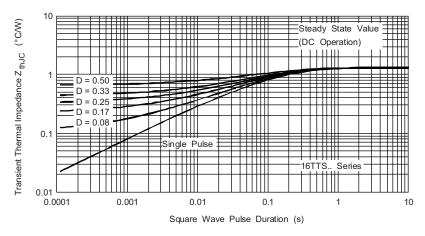


Fig. 8 - Thermal Impedance Z_{thJC} Characteristics

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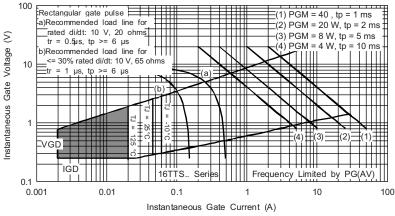
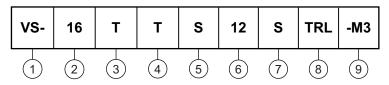


Fig. 9 - Gate Characteristics

ORDERING INFORMATION TABLE

Device code



- 1 Vishay Semiconductors product
- 2 Current rating
- Circuit configuration:
 - T = single thyristor
- 4 Package:
 - $T = D^2PAK (TO-263AB)$
- 5 Type of silicon:
 - S = standard recovery rectifier
- 08 = 800 V 12 = 1200 V
- 7 S = surface mountable
- 8 • None = tube
 - TRL = tape and reel (left oriented)
 - TRR = tape and reel (right oriented)
- 9 -M3 = halogen-free, RoHS-compliant, and terminations lead (Pb)-free

ORDERING INFORMATION (Example)									
PREFERRED P/N	BASE QUANTITY	PACKAGING DESCRIPTION							
VS-16TTS08S-M3	50	Antistatic plastic tubes							
VS-16TTS08STRL-M3	800	13" diameter plastic tape and reel							
VS-16TTS08STRR-M3	800	13" diameter plastic tape and reel							
VS-16TTS12S-M3	50	Antistatic plastic tubes							
VS-16TTS12STRL-M3	800	13" diameter plastic tape and reel							
VS-16TTS12STRR-M3	800	13" diameter plastic tape and reel							

LINKS TO RELATED DOCUMENTS					
Dimensions	www.vishay.com/doc?96164				
Part marking information	www.vishay.com/doc?95444				
Packaging information	www.vishay.com/doc?96424				
SPICE model	www.vishay.com/doc?96772				



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D²PAK

DIMENSIONS in millimeters and inches



SYMBOL	MILLIM	ETERS	INC	HES	NOTES	SYMBOL	MILLIM	ETERS	INC	HES	NOTES	
STIVIBUL	MIN.	MAX.	MIN.	MAX.	NOIES	NOTES	STINIBUL	MIN.	MAX.	MIN.	MAX.	NOTES
Α	4.06	4.83	0.160	0.190			D1	6.86	8.00	0.270	0.315	3
A1	0.00	0.254	0.000	0.010			E	9.65	10.67	0.380	0.420	2, 3
b	0.51	0.99	0.020	0.039			E1	7.90	8.80	0.311	0.346	3
b1	0.51	0.89	0.020	0.035	4		е	2.54	BSC	0.100	BSC	
b2	1.14	1.78	0.045	0.070			Н	14.61	15.88	0.575	0.625	
b3	1.14	1.73	0.045	0.068	4		L	1.78	2.79	0.070	0.110	
С	0.38	0.74	0.015	0.029			L1	-	1.65	-	0.066	3
c1	0.38	0.58	0.015	0.023	4		L2	1.27	1.78	0.050	0.070	
c2	1.14	1.65	0.045	0.065			L3	0.25	BSC	0.010	BSC	
D	8.51	9.65	0.335	0.380	2		L4	4.78	5.28	0.188	0.208	

Notes

- (1) Dimensioning and tolerancing per ASME Y14.5 M-1994
- (2) Dimension D and E do not include mold flash. Mold flash shall not exceed 0.127 mm (0.005") per side. These dimensions are measured at the outmost extremes of the plastic body
- (3) Thermal pad contour optional within dimension E, L1, D1 and E1
- (4) Dimension b1 and c1 apply to base metal only
- (5) Datum A and B to be determined at datum plane H
- (6) Controlling dimension: inches
- (7) Outline conforms to JEDEC® outline TO-263AB

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